

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Reissue patent application of :  
Oh-Sung SONG et al. : **BOX REISSUE**  
Serial No. (new)<sup>1</sup> :  
Filed June 30, 2003 :

METHOD FOR FABRICATING MOS SEMICONDUCTOR DEVICE HAVING SALICIDE REGION  
AND LDD REGION

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**AMENDMENT ACCOMPANING  
REISSUE APPLICATION**

Honorable Commissioner For Patents  
Washington, D.C. 20231

Sir:

Concurrently with the filing of the above-identified reissue application, the  
following amendments and remarks are submitted:

In the Claims

***Kindly add the following new Claims 9-17:***

9. (New) A method for fabricating a metal oxide semiconductor (MOS) transistor,  
comprising:

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<sup>1</sup> This is a reissue application of U.S. Patent No. 6,255,181 B1, issued July 3, 2001.